

RJK5003DPD

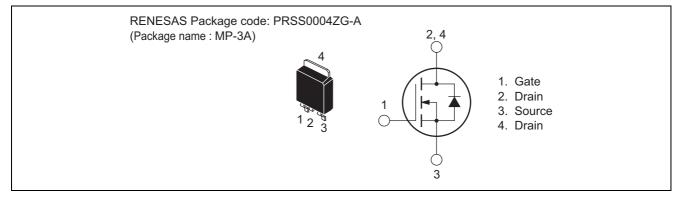
Silicon N Channel Power MOS FET High Speed Power Switching Use

> REJ03G0580-0300 Rev.3.00 Dec 19, 2008

Features

- V_{DSS} : 500 V
- R_{DS(on)} : 1.5 Ω (MAX.)
- I_D: 5 A
- Surface mount package (MP-3A)

Outline



Applications

• Lighting ballast, SMPS, etc.

Maximum Ratings

 $(Tc = 25^{\circ}C)$

Parameter	Symbol	Ratings	Unit	Conditions
Drain to source voltage	V _{DSS}	500	V	$V_{GS} = 0 V$
Gate to source voltage	V _{GSS}	±30	V	$V_{DS} = 0 V$
Drain current	ID	5	А	
Drain Peak current	I _{D (pulse)} Note1	20	Α	
Avalanche current	I _{AP}	5	А	L = 200 μH
Channel dissipation	Pch	62.5	W	
Channel temperature	Tch	150	°C	
Storage temperature	Tstg	-55 to +150	°C	
Channel to case thermal impedance	θ_{ch-c}	2.0	°C/W	Channel to case

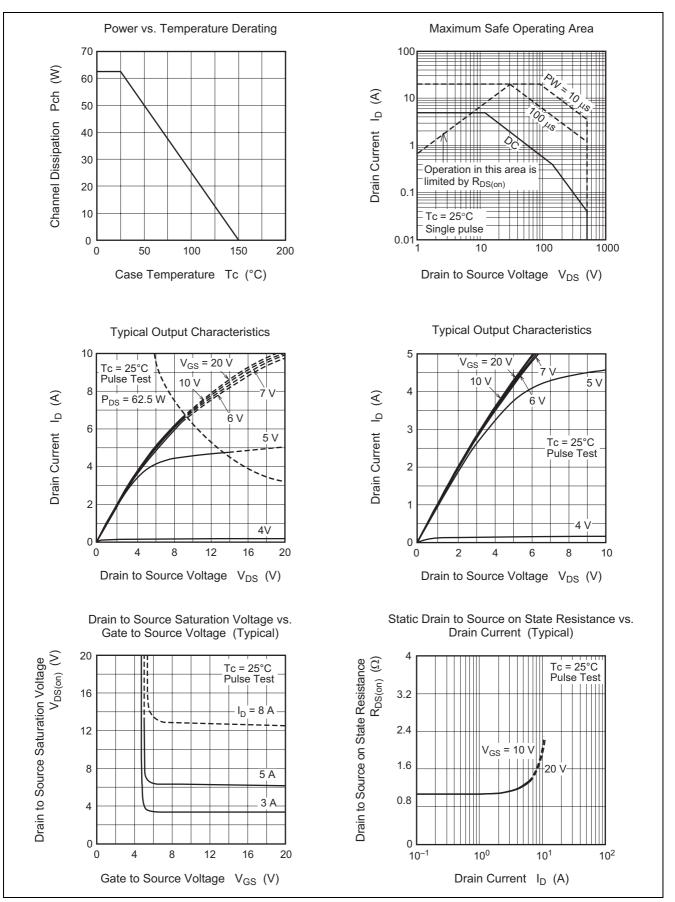
Note: 1. Pulse width limited by safe operating area.

Electrical Characteristics

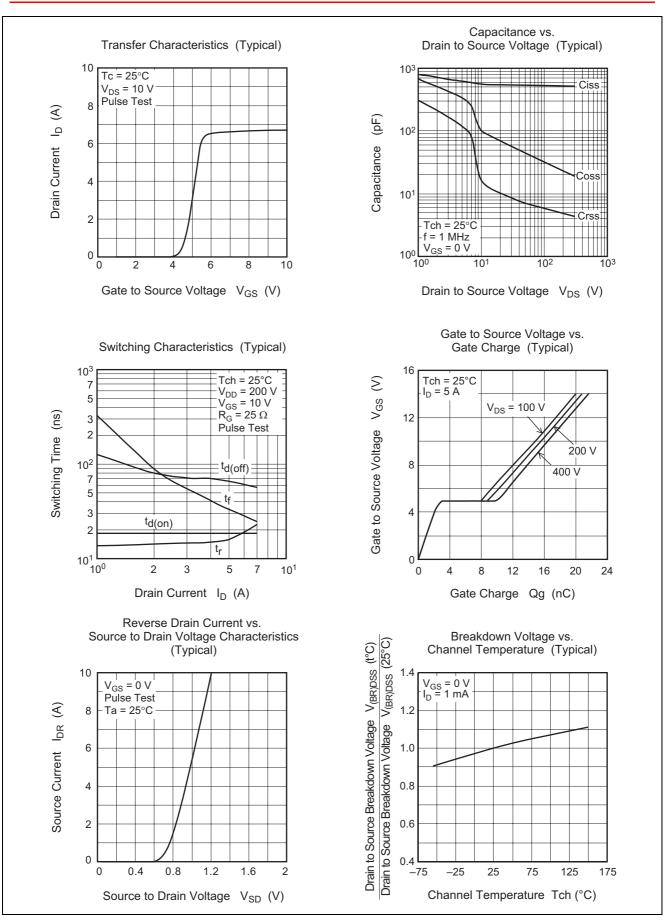
						$(Tch = 25^{\circ}C)$
Parameter	Symbol	Min.	Тур.	Max.	Unit	Test conditions
Drain to source breakdown voltage	V _{(BR)DSS}	500		—	V	$I_D = 1 \text{ mA}, V_{GS} = 0 \text{ V}$
Zero gate voltage drain current	I _{DSS}	_		1	mA	$V_{DS} = 500 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$
Gate to source leak current	I _{GSS}	_		±0.1	μΑ	$V_{GS}=\pm25~V,~V_{DS}=0~V$
Gate to source cutoff voltage	V _{GS(off)}	3.0	3.5	4.0	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$
Static drain to source on state	R _{DS(on)}	_	1.3	1.5	Ω	I_{D} = 2 A, V_{GS} = 10 V^{Note2}
resistance						
Input capacitance	Ciss	_	550	—	pF	$V_{DS} = 25 \text{ V}, \text{ V}_{GS} = 0 \text{ V},$ f = 1 MHz
Output capacitance	Coss	_	60	—	pF	
Reverse transfer capacitance	Crss	_	10	—	pF	
Turn-on delay time	t _{d(on)}	_	20	—	ns	$\begin{split} V_{DD} &= 200 \ V, \ I_D = 2 \ A, \\ V_{GS} &= 10 \ V \\ R_G &= 25 \ \Omega \end{split}$
Rise time	tr	_	20	—	ns	
Turn-off delay time	t _{d(off)}	_	60	—	ns	
Fall time	t _f	_	25	—	ns	
Body-drain diode forward voltage	V _{DF}	—	1.0	1.5	V	$I_F = 2 \text{ A}, V_{GS} = 0 \text{ V}^{Note2}$

Note: 2. Pulse test

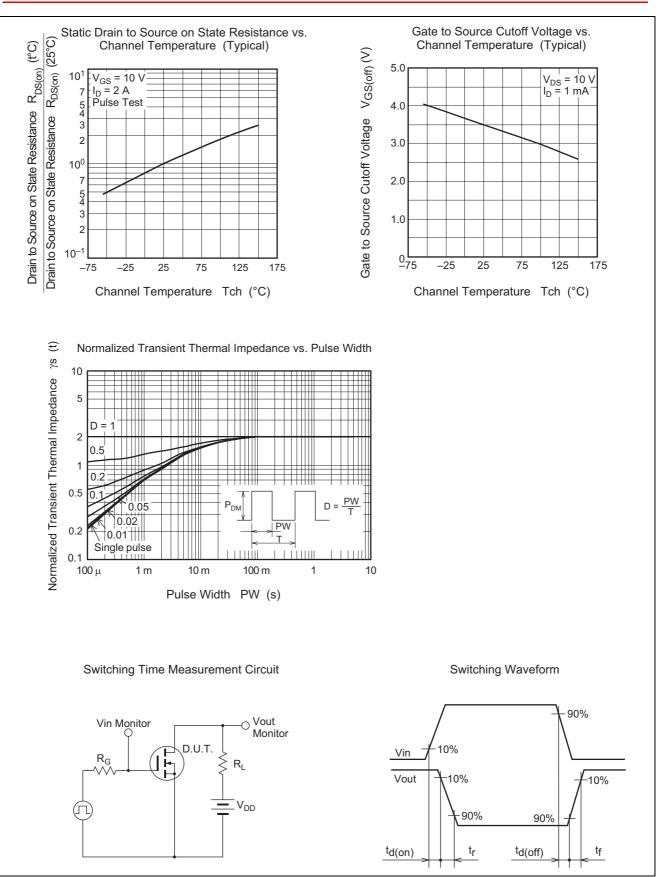
Main Characteristics



RENESAS

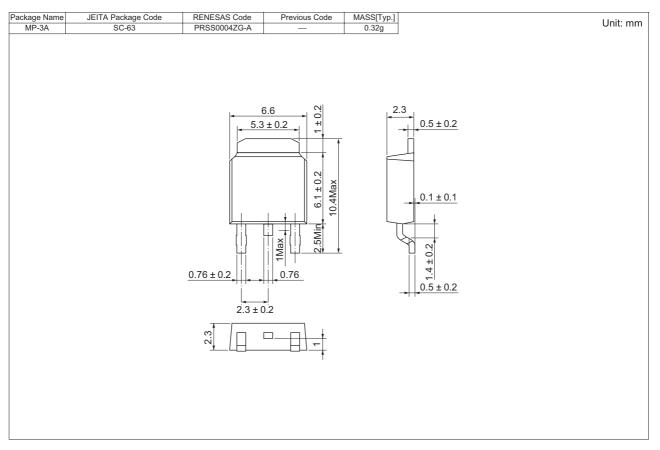


RENESAS



RENESAS

Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
RJK5003DPD-00-J2	3000 pcs	Taping

RenesasTechnology Corp. sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

- Benesas lechnology Corp. sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
 Pines
 This document is provided for reference purposes only so that Renesas customers may select the appropriate Renesas products for their use. Renesas neither makes warranties or representations with respect to the accuracy or completeness of the information in this document.
 But not infinited to, product data. diagrams, charts, programs, algorithms, and application scuch as the development of weapons of mass and regulations, and proceedures required by such laws and regulation.
 All information in this document, included in this document for the purpose of military application scuch as the development of weapons of mass and regulations, and proceedures required by such laws and regulations.
 All information included in this document such as product data, diagrams, charts, programs, algorithms, and application carcuit examples, is current as of the date this document, when exporting the products or the technology described herein, you should follow the applicable export control laws and regulations, and proceedures required by such laws and regulations.
 Renesas has used reasonable care in compiling the information in this document, but Renesas assumes no liability whatsoever for any damages incurred as a fast stude of the document. You should evaluate the information in light of the total system before deciding about the applicability or there were provided specific by series as subal table. The subality of the series of the subality of the series of the subality of the series as subality of the series of any damages incurred as a state of the date this document.
 When using or otherwise regulations in the information in this document. Dut Renesas as subality of that series of any damages incurred as a state of otherwise systems for transportation and traffic by the series of the series of the series of the series of the



RENESAS SALES OFFICES

Refer to "http://www.renesas.com/en/network" for the latest and detailed information.

Renesas Technology America, Inc.

450 Holger Way, San Jose, CA 95134-1368, U.S.A Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K. Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology (Shanghai) Co., Ltd. Unit 204, 205, AZIACenter, No.1233 Lujiazui Ring Rd, Pudong District, Shanghai, China 200120 Tel: <86> (21) 5877-1818, Fax: <86> (21) 6887-7858/7898

Renesas Technology Hong Kong Ltd. 7th Floor, North Tower, World Finance Centre, Harbour City, Canton Road, Tsimshatsui, Kowloon, Hong Kong Tel: <852> 2265-6688, Fax: <852> 2377-3473

Renesas Technology Taiwan Co., Ltd. 10th Floor, No.99, Fushing North Road, Taipei, Taiwan Tel: <886> (2) 2715-2888, Fax: <886> (2) 3518-3399

Renesas Technology Singapore Pte. Ltd.

1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632 Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd. Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

Renesas Technology Malaysia Sdn. Bhd Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: <603> 7955-9390, Fax: <603> 7955-9510

http://www.renesas.com